

CMOS-CCD 1H/2H Delay Line for NTSC

Description

The CXL5509M/P is a CMOS-CCD delay line developed for video signal processing. Usage in conjunction with an external low-pass filter provide 1H and 2H delay signals simultaneously (For NTSC signals).

Features

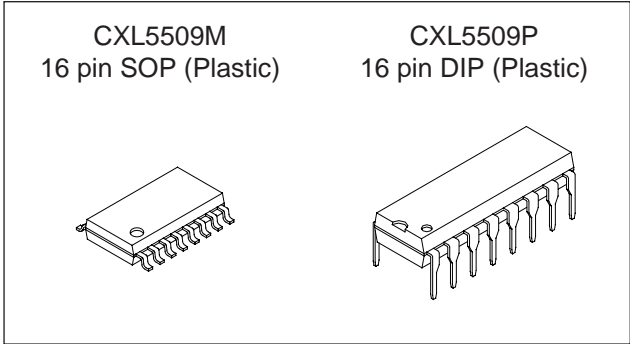
- Single power supply (5V)
- Low power consumption 130mW (Typ.)
- Built-in peripheral circuits
- Built-in quadruple PLL circuit
- For NTSC signals
- 1 input and 2 outputs
- (Outputs for both 1H and 2H delays)

Functions

- 906-bit (1H) and 1816-bit (2H) CCD register
- Clock driver
- Auto-bias circuit
- Sync tip clamp circuit
- Sample-and-hold circuit
- Quadruple PLL circuit

Structure

CMOS-CCD



Absolute Maximum Ratings (Ta = 25°C)

• Supply voltage	V _{DD}	6	V
• Operating temperature	T _{opr}	-10 to +60	°C
• Storage temperature	T _{stg}	-55 to +150	°C
• Allowable power dissipation	P _D		
	CXL5509M	400	mW
	CXL5509P	800	mW

Recommended Operating Condition (Ta = 25°C)

Supply voltage	V _{DD}	5 ± 5%	V
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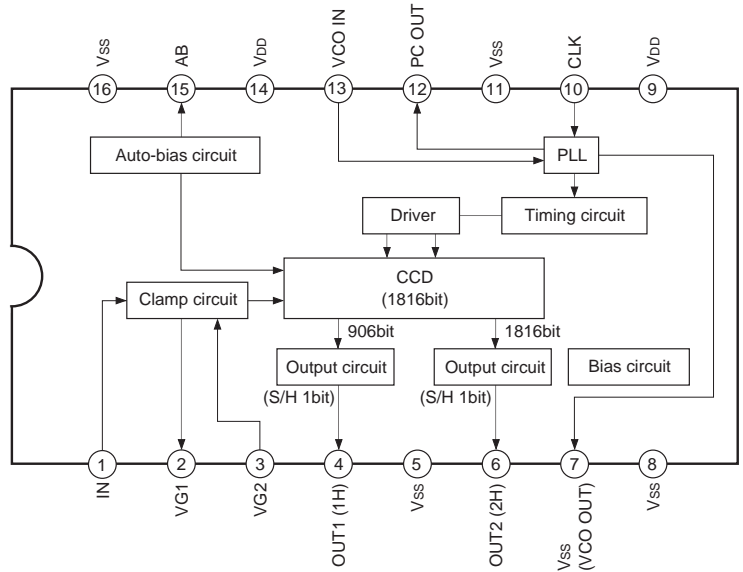
Recommended Clock Conditions (Ta = 25°C)

- Input clock amplitude V_{CLK} 0.3 to 1.0 V_{p-p}
(0.5V_{p-p} typ.)
- Clock frequency f_{CLK} 3.579545 MHz
- Input clock waveform sine wave

Input Signal Amplitude

V_{SIG} 571mV_{p-p} (Max.) (at internal clamp condition)

Block Diagram and Pin Configuration (Top View)



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Pin Description

Pin No.	Symbol	I/O	Description	Impedance
1	IN	I	Signal input (Non-inverted signal)	> 10k Ω (at no clamp)
2	VG1	O	Gate bias 1 DC output	
3*	VG2	I	Gate bias 2 DC input	
4	OUT1	O	1H signal output (Inverted signal)	40 to 500 Ω
5	V _{SS}	—	GND	
6	OUT2	O	2H signal output (Inverted signal)	40 to 500 Ω
7	V _{SS} (VCO OUT)	(O)	GND or VCO output (4fsc)	
8	V _{SS}	—	GND	
9	V _{DD}	—	Power supply (5V)	
10	CLK	I	Clock input (fsc)	> 10k Ω
11	V _{SS}	—	GND	
12	PC OUT	O	Phase comparator output	
13	VCO IN	I	VCO input	
14	V _{DD}	—	Power supply (5V)	
15	AB	O	Autobias DC output	600 to 200k Ω
16	V _{SS}	—	GND	

* Description of Pin 3 (VG2)

Control of input signal clamp condition

0V Sync tip clamp condition

5V Center bias condition

The input signal is biased to approx. 2.1V by means of the IC internal resistance (approx. 10k Ω).
In this mode, the input signal is limited to APL 50% and the maximum input signal amplitude is at 200mVp-p.

Electrical Characteristics

(Ta = 25°C, V_{DD} = 5V, f_{CLK} = 3.579545MHz, V_{CLK} = 500mVp-p, sine wave)

See "Electrical Characteristics Test Circuit"

Item	Symbol	Test conditions (Note 1)	SW conditions				Min.	Typ.	Max.	Unit	Note
			1	2	3	4					
Supply current	I _{DD}	—	a	b	a	a	16	26	36	mA	2
Low frequency gain	GL1	200kHz, 500mVp-p, sine wave	a	b	a	b	-2	0	2	dB	3
	GL2		a	b	b	b	-2	0	2		
Frequency response	fR1	200kHz ↔ 3.58MHz, 150mVp-p, sine wave	b ↔ c	a	a	b	-2.0	-1.0	0	dB	4
	fR2		b ↔ c	a	b	b	-2.0	-1.0	0		
Differential gain	DG1	5-staircase wave	d	b	a	c	—	3	5	%	5
	DG2		d	b	b	c	—	3	5		
Differential phase	DP1	5-staircase wave	d	b	a	c	—	3	5	degree	5
	DP2		d	b	b	c	—	3	5		
S/N ratio	SN1	50% white video signal	e	b	a	d	52	56	—	dB	6
	SN2		e	b	b	d	52	56	—		
S/H pulse coupling	CP1	No signal input	f	b	a	a	—	—	350	mVp-p	7
	CP2		f	b	b	a	—	—	350		

Notes

(1) By switching SW2, input condition turns out as follows.

SW2 condition	Input condition
a	Center bias condition (approx. 2.1V) Approx. 2.1V bias is applied internally to the input signal
b	Sync tip clamp conditions

(2) This is the IC supply current value during clock and signal input.

(3) GL is the output gain of OUT pin when a 500mVp-p, 200kHz sine wave is fed to IN pin.

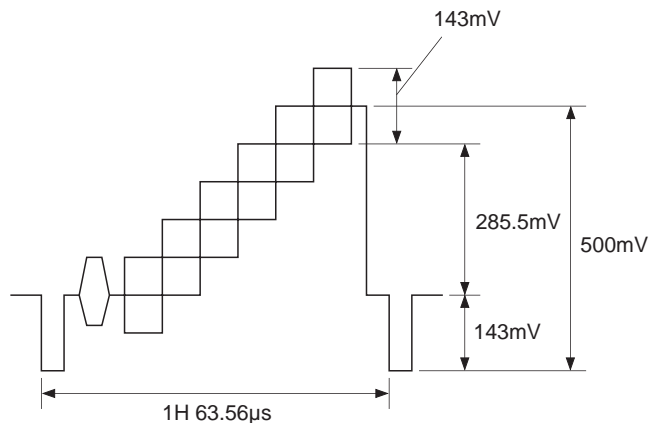
$$GL = 20 \log \frac{\text{OUT pin output voltage [mVp-p]}}{500 \text{ [mVp-p]}} \text{ [dB]}$$

(4) Indicates the dissipation at 3.58MHz in relation to 200kHz.

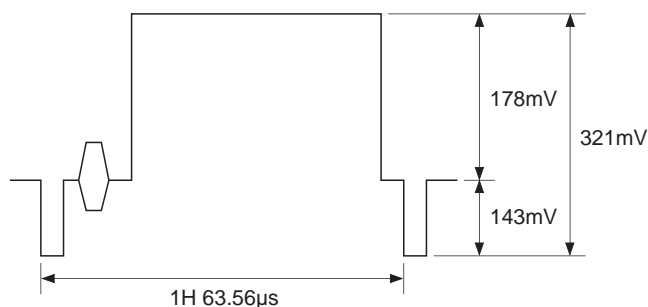
From the output voltage at OUT pin when a 150mVp-p, 200kHz sine wave is fed to IN pin, and from the output voltage at OUT pin when a 150mVp-p, 3.58MHz sine wave is fed to same, calculation is made according to the following formula.

$$fR = 20 \log \frac{\text{OUT pin output voltage (3.58MHz) [mVp-p]}}{\text{OUT pin output voltage (200kHz) [mVp-p]}} \text{ [dB]}$$

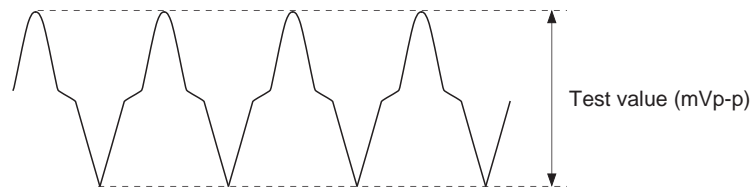
(5) The differential gain (DG) and the differential phase (DP), when the 5-staircase wave in the following figure is fed, are tested with a vector scope:



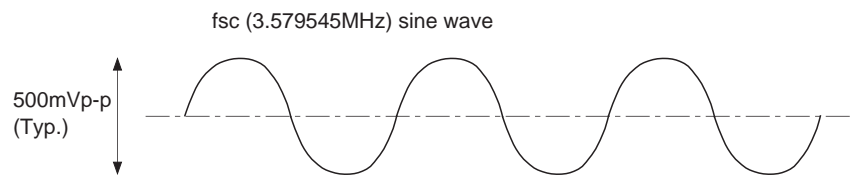
(6) S/N ratio during 50% white video signal input shown in figure below is tested at video noise meter, in BPF 100kHz to 4MHz, Sub Carrier Trap mode.



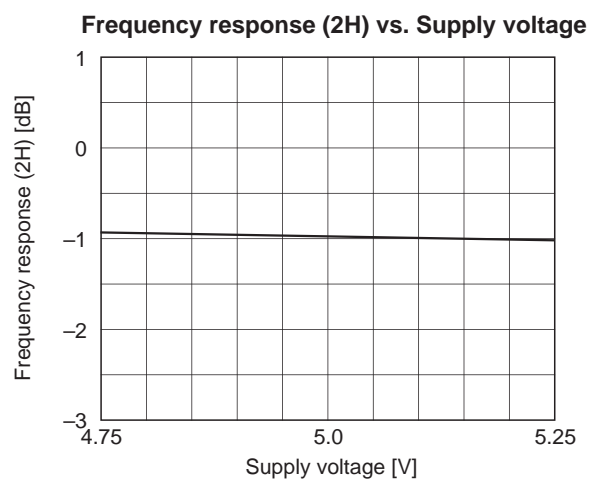
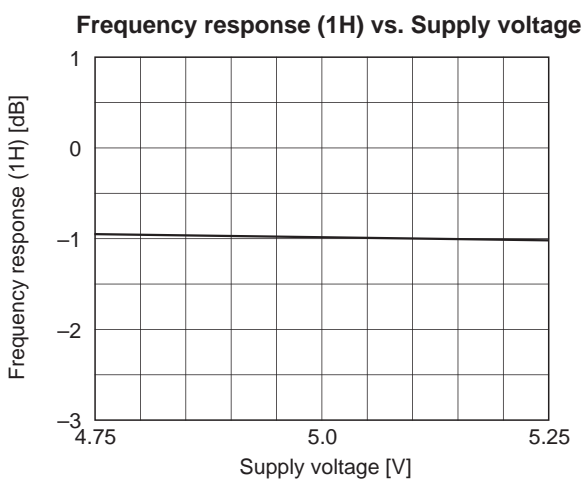
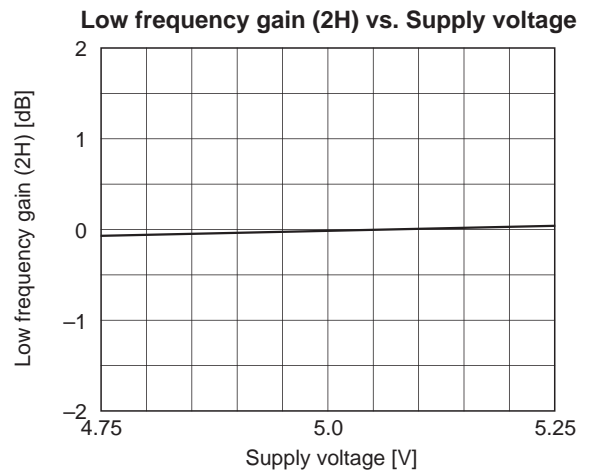
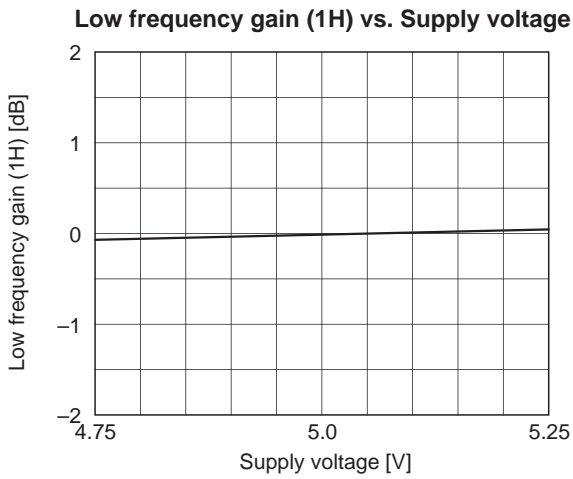
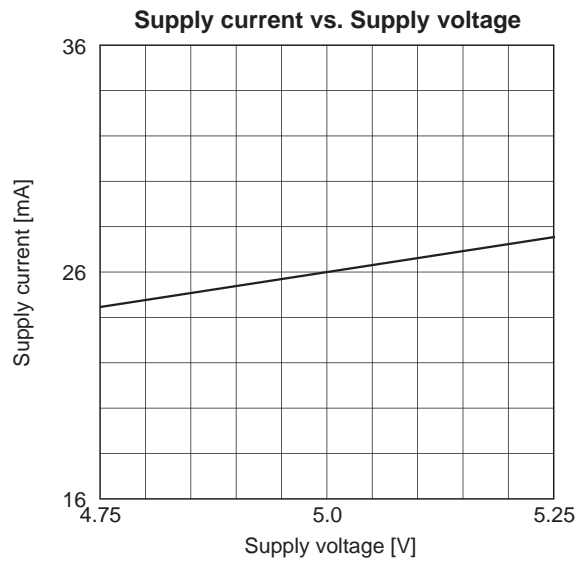
- (7) The internal clock component to the output signal during no-signal input and the leakage of that high harmonic component are tested.

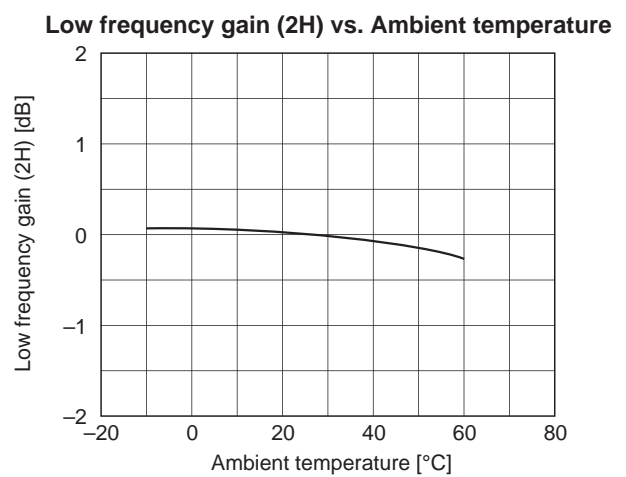
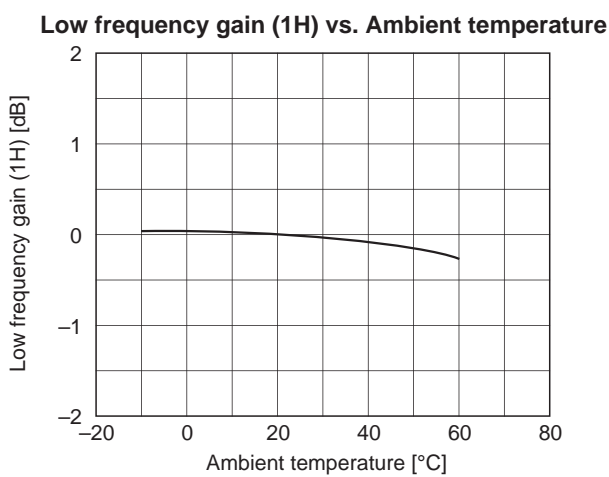
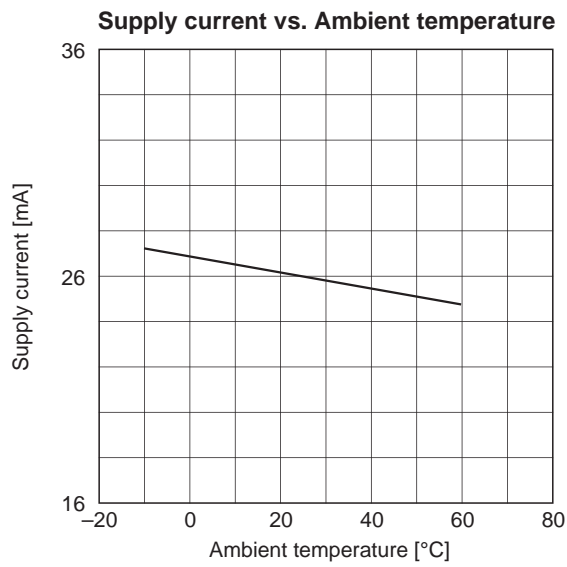
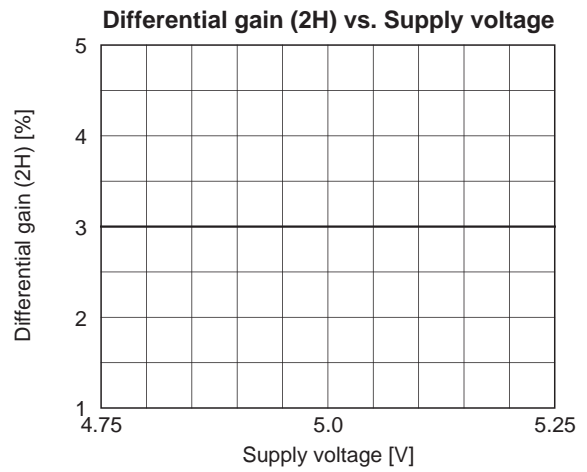
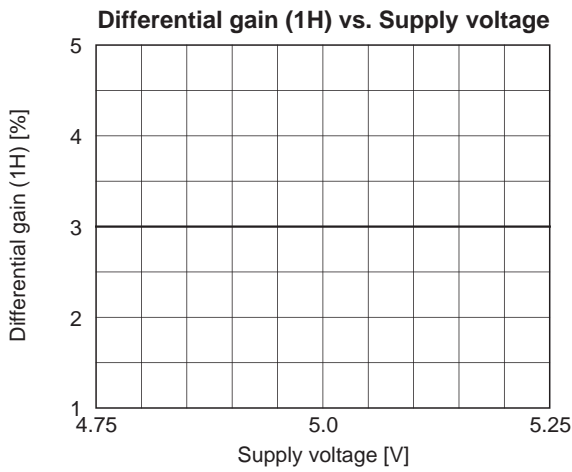


Clock

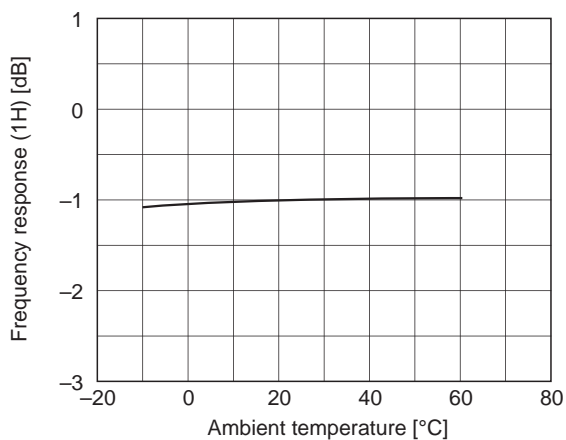


Example of Representative Characteristics

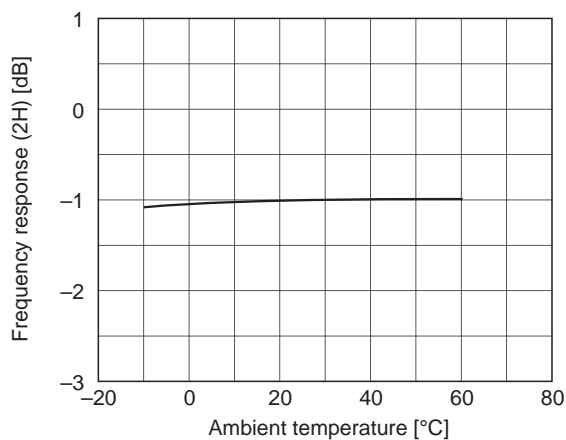




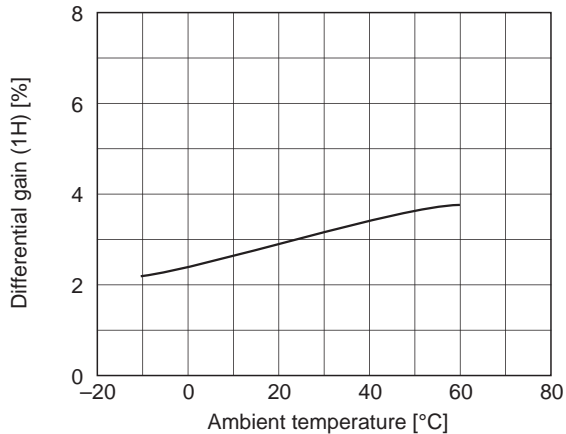
Frequency response (1H) vs. Ambient temperature



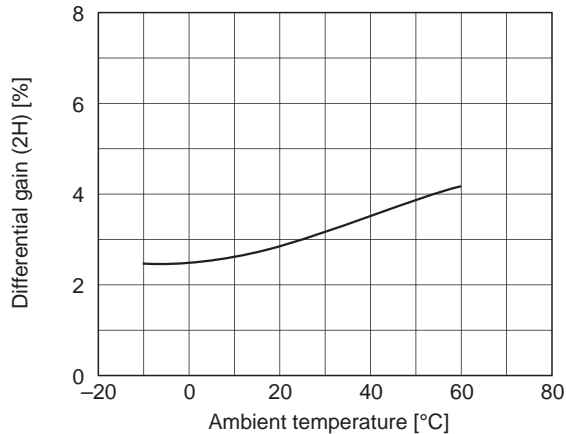
Frequency response (2H) vs. Ambient temperature

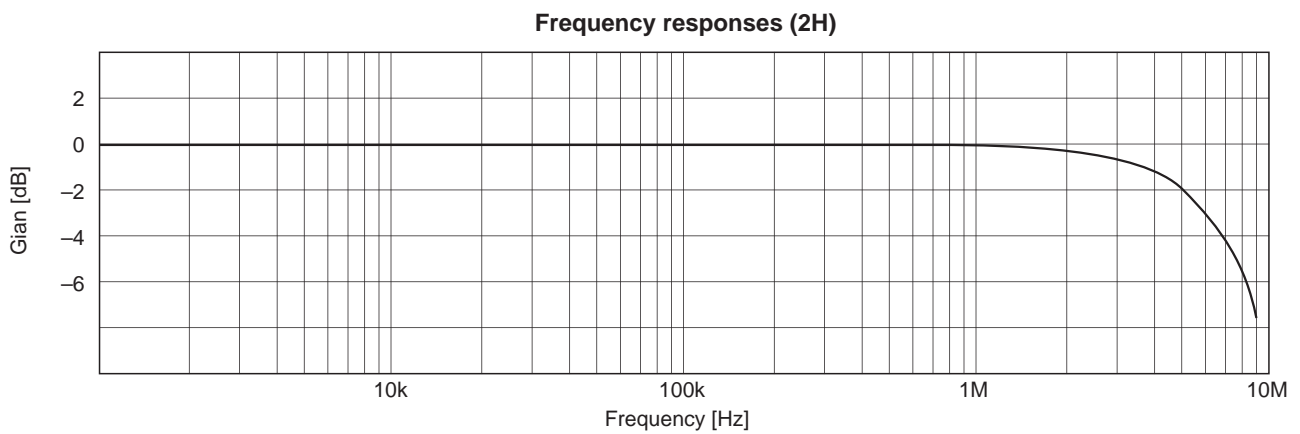
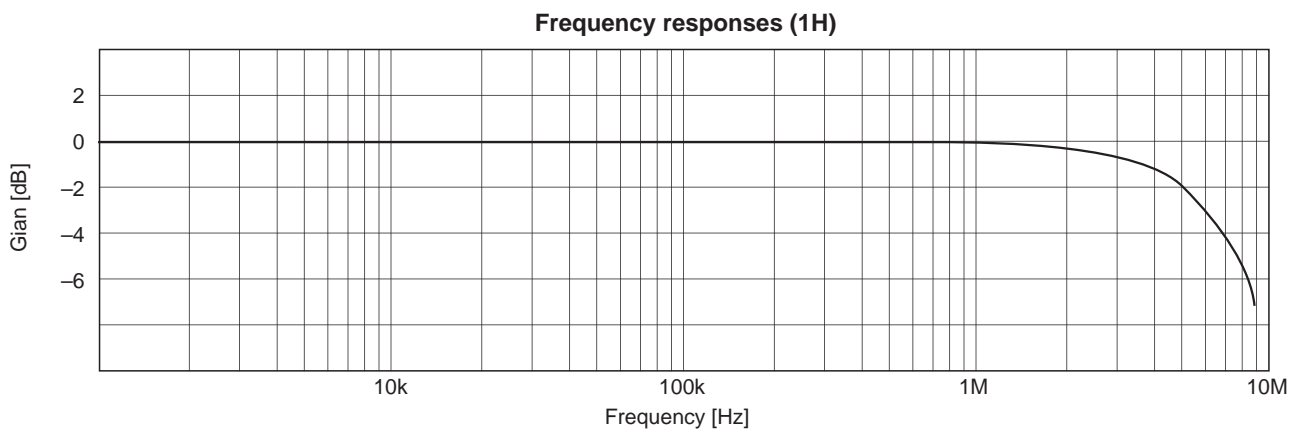


Differential gain (1H) vs. Ambient temperature



Differential gain (2H) vs. Ambient temperature



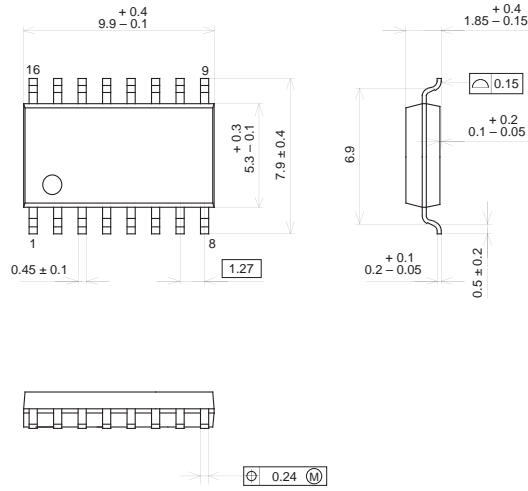


Note) 1H means 1H output; 2H means 2H output.

Package Outline Unit: mm

CXL5509M

16PIN SOP (PLASTIC)



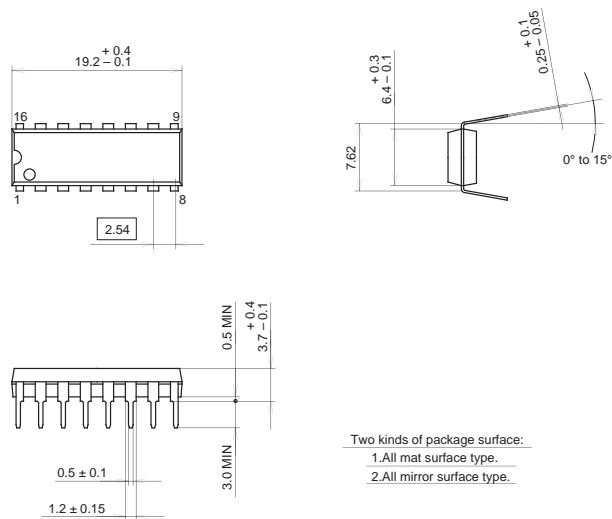
SONY CODE	SOP-16P-L01
EIAJ CODE	SOP016-P-0300
JEDEC CODE	

PACKAGE STRUCTURE

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE MASS	0.2g

CXL5509P

16PIN DIP (PLASTIC)



SONY CODE	DIP-16P-01
EIAJ CODE	DIP016-P-0300
JEDEC CODE	Similar to MO-001-AE

PACKAGE STRUCTURE

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE MASS	1.0 g